

Silicon Epitaxial Planar Schottky Barrier Diode

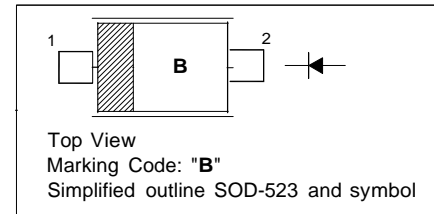
for low current rectification and high speed switching applications

Features

- Extremely small surface mounting type
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



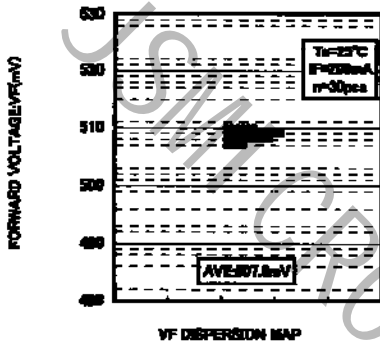
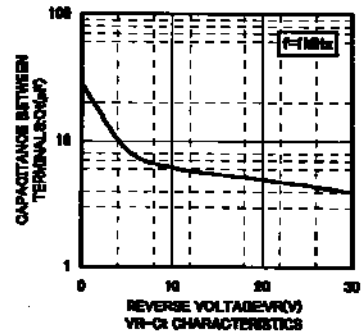
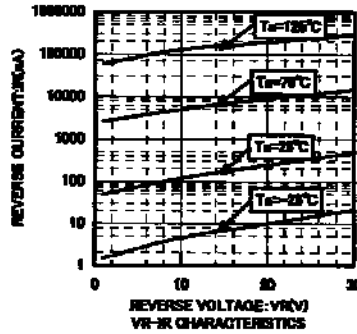
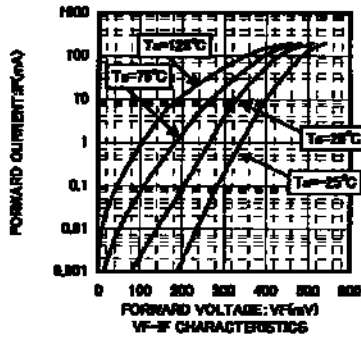
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Mean Rectifying Current	$I_{F(AV)}$	200	mA
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I_{FSM}	1	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^\circ\text{C}$

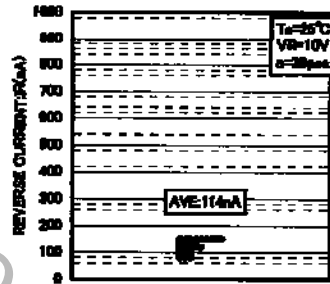
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	0.6	V
Reverse Current at $V_R = 10\text{ V}$	I_R	1	μA

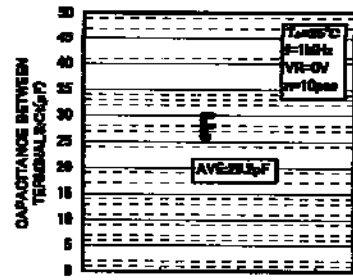
Note: ESD sensitive product handling required.



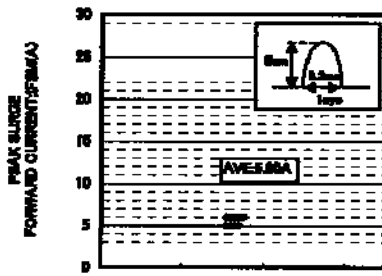
VF DISPERSION MAP



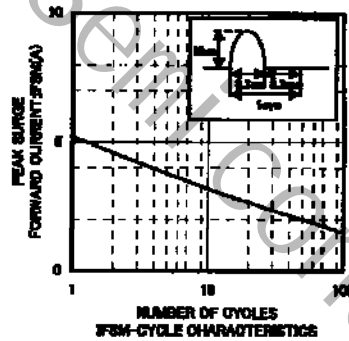
IR DISPERSION MAP



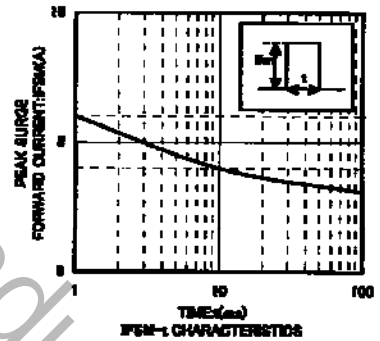
Cr DISPERSION MAP



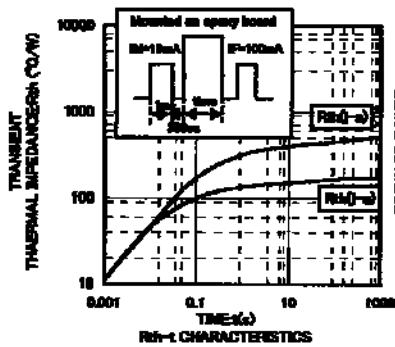
IFSM DISPERSION MAP



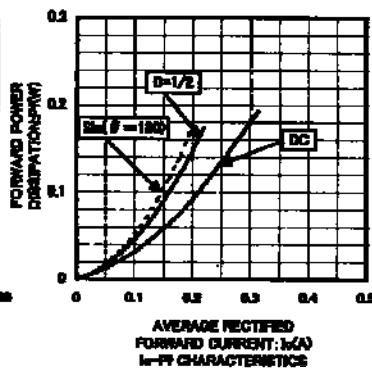
IFSM-CYCLE CHARACTERISTICS



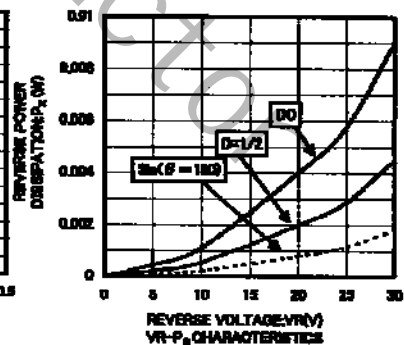
IFSM-t CHARACTERISTICS



Rth-t CHARACTERISTICS



Ia-Pf CHARACTERISTICS



VR-Po CHARACTERISTICS

PACKAGE OUTLINE

SOD-523

Plastic surface mounted package; 2 leads

